



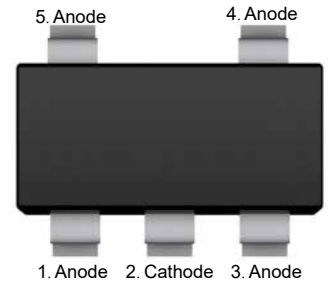
MMBN187SE

Silicon Epitaxial Planar Switching Diode

Features:

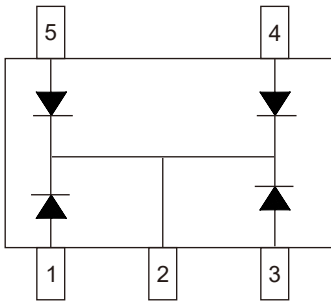
- High Speed switching

Package: SMD-5



Marking Code: N187

Electrical Symbol:



Maximum Ratings (at T_J = 25°C unless otherwise specified):

Parameter	Symbol	Value	Unit
Maximum Repetitive Reverse Voltage	V _{RRM}	80	V
Reverse Voltage	V _R	80	V
Average Rectified Forward Current	I _{F(AV)}	100	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	1 4	A
		at t = 1s	
		at t = 1μs	
Maximum Power Dissipation	P _D	350	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Electrical Characteristics (at T_J = 25°C unless otherwise specified):

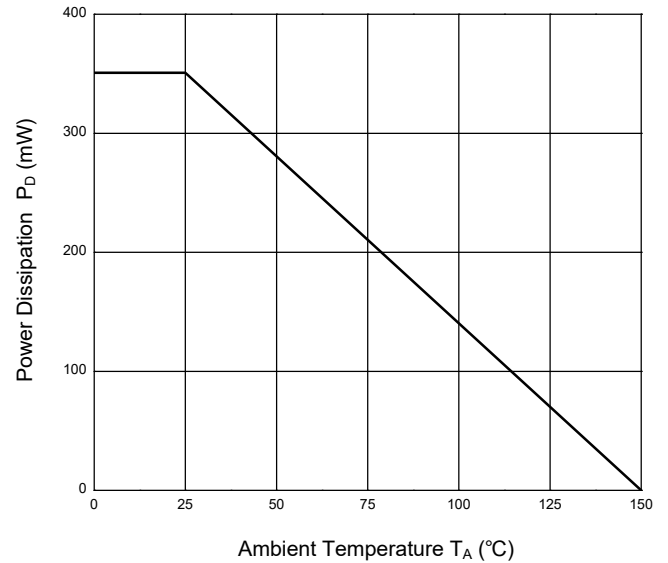
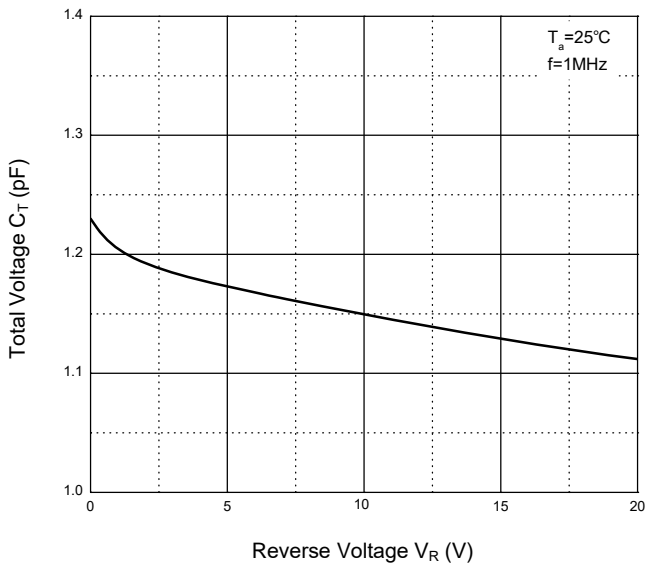
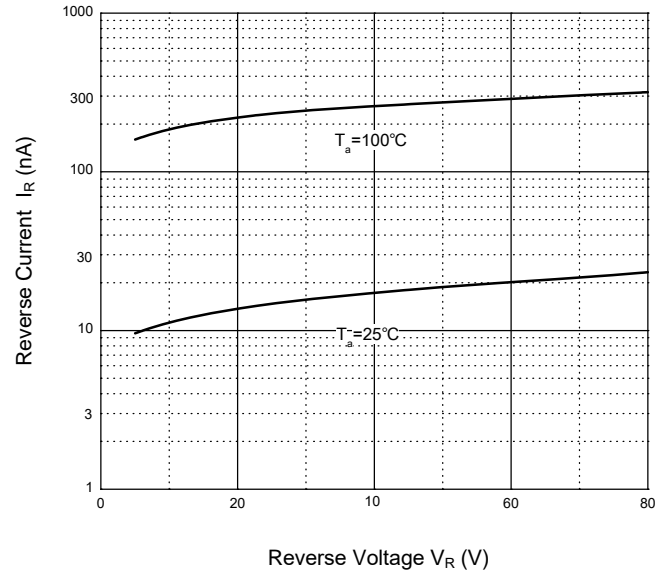
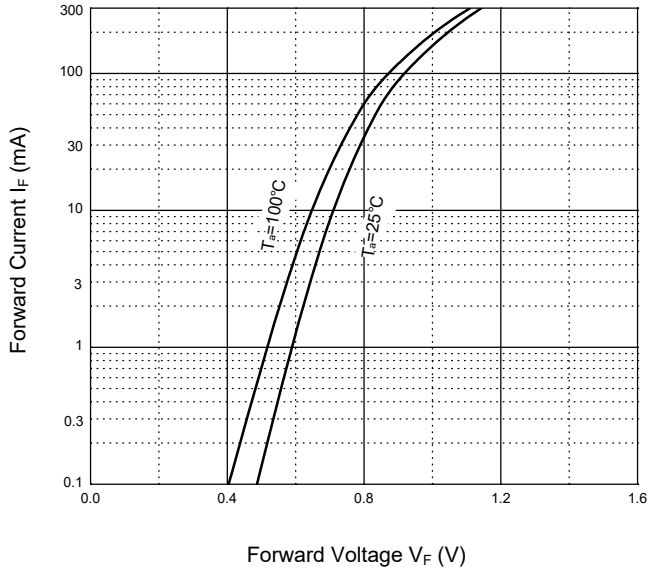
Parameter	Symbol	Min.	Max.	Unit
Forward Voltage	V _F	--	0.7	V
at I _F = 5 mA		--		
at I _F = 10 mA		--	0.85	
Reverse Breakdown Voltage at I _R = 100 μA	V _{(BR)R}	80	--	
Reverse Current at V _R = 80 V	I _R	--	1	μA
Typical Junction Capacitance	C _j	--	3	pF
at V _R = 0 V, f = 1 MHz				
Maximum Reverse Recovery Time	T _{rr}	--	4	nS
at I _F = I _R = 10mA, I _{rr} = 0.1×I _R				



MMBN187SE[†]

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Typical Characteristic Curves





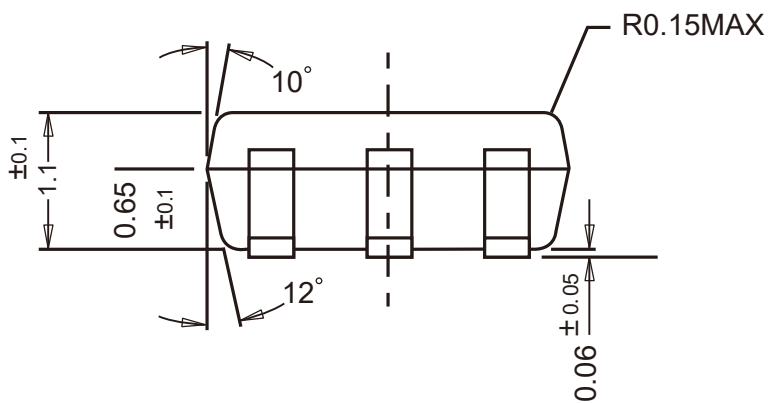
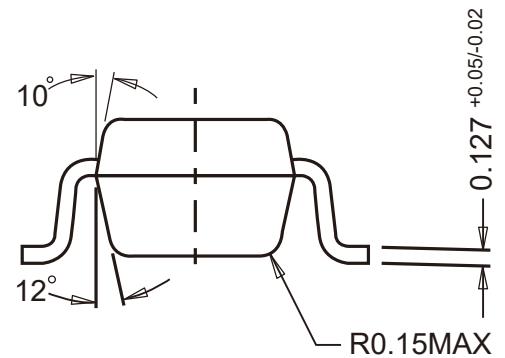
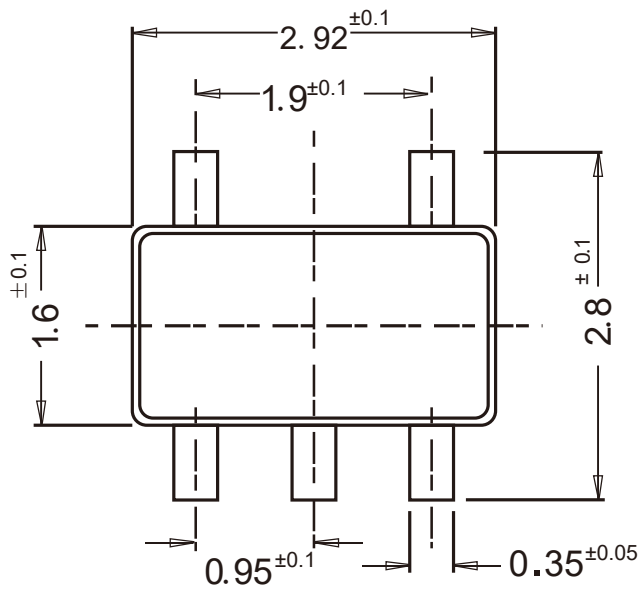
MMBN187SE[†]

Silicon Epitaxial Planar Switching Diode

Package Outline

SOT-23-5

Dimensions in mm



Ordering Information

Device	Package	Shipping
MMBN187SE	SOT-23-5	3,000PCS/Reel&7inches